## NPN SILICON TRIPLE DIFFUSED TRANSISTOR FOR HIGH－SPEED HIGH－VOLTAGE SWITCHING

The 2SC2335 is a mold power transistor developed for high－speed high－voltage switching，and is ideal for use as a driver in devices such as switching regulators，DC／DC converters，and high－frequency power amplifiers．

## FEATURES

－Low collector saturation voltage：Vce（sat）＝1．0 V MAX．＠lc＝3．0 A
－Fast switching speed： $\mathrm{tf}_{\mathrm{f}}=1.0 \mu \mathrm{~s}$ MAX．＠Ic＝ 3.0 A
－Wide base reverse－bias SOA：VCEx（SUs）1＝450 V MIN．＠Ic＝3．0 A
ABSOLUTE MAXIMUM RATINGS（ $\mathrm{T}_{\mathrm{A}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ ）

| Parameter | Symbol | Conditions | Ratings | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Collector to base voltage | Vсво |  | 500 | V |
| Collector to emitter voltage | V ${ }_{\text {ceo }}$ |  | 400 | V |
| Emitter to base voltage | Vebo |  | 7.0 | V |
| Collector current（DC） | $\mathrm{IC}(\mathrm{DC)}$ |  | 7.0 | A |
| Collector current（pulse） | $\mathrm{I}^{\text {c（pulse）}}$ | $\begin{aligned} & \mathrm{PW} \leq 300 \mu \mathrm{~s}, \\ & \text { duty cycle } \leq 10 \% \end{aligned}$ | 15 | A |
| Base current（DC） | $\mathrm{lb}(\mathrm{DC})$ |  | 3.5 | A |
| Total power dissipation | $\mathrm{P}_{\text {T }}$ | $\mathrm{Tc}=25^{\circ} \mathrm{C}$ | 40 | W |
|  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | 1.5 | W |
| Junction temperature | $\mathrm{T}_{\mathrm{j}}$ |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | $\mathrm{T}_{\text {stg }}$ |  | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

ORDERING INFORMATION

| Part No． | Package |
| :---: | :---: |
| 2 SC2335 | TO－220AB |

（TO－220AB）


## ELECTRICAL CHARACTERISTICS (TA $=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector to emitter voltage | Vceo(sus) | $\mathrm{Ic}=3.0 \mathrm{~A}, \mathrm{IB} 1=0.6 \mathrm{~A}, \mathrm{~L}=1 \mathrm{mH}$ | 400 |  |  | V |
| Collector to emitter voltage | $\mathrm{V}_{\text {cEx(SUS) }}$ | $\begin{aligned} & \mathrm{IC}_{\mathrm{C}}=3.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B} 1}=-\mathrm{I}_{\mathrm{B} 2}=0.6 \mathrm{~A}, \\ & \mathrm{~V}_{\text {BE(OFF) }}=-5.0 \mathrm{~V}, \mathrm{~L}=180 \mu \mathrm{H}, \text { clamped } \end{aligned}$ | 450 |  |  | V |
| Collector to emitter voltage | $\mathrm{V}_{\text {cEx(SUS)2 }}$ | $\begin{aligned} & \mathrm{IC}_{\mathrm{C}}=6.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B} 1}=2.0 \mathrm{~A},-\mathrm{I}_{\mathrm{B} 2}=0.6 \mathrm{~A}, \\ & \mathrm{~V}_{\text {BE(OFF) }}=-5.0 \mathrm{~V}, \mathrm{~L}=180 \mu \mathrm{H}, \text { clamped } \end{aligned}$ | 400 |  |  | V |
| Collector cutoff current | Ісво | $\mathrm{V}_{\text {CB }}=400 \mathrm{~V}, \mathrm{le}=0 \mathrm{~A}$ |  |  | 10 | $\mu \mathrm{A}$ |
| Collector cutoff current | Icer | $\mathrm{V}_{\text {ce }}=400 \mathrm{~V}, \mathrm{R}_{\text {be }}=51 \Omega, \mathrm{~T}_{\mathrm{A}}=125^{\circ} \mathrm{C}$ |  |  | 1.0 | mA |
| Collector cutoff current | IcEx1 | $\mathrm{V}_{\text {ce }}=400 \mathrm{~V}, \mathrm{~V}_{\text {be(OFF) }}=-1.5 \mathrm{~V}$ |  |  | 10 | $\mu \mathrm{A}$ |
| Collector cutoff current | Icex2 | $\begin{aligned} & V_{\text {CE }}=400 \mathrm{~V}, \mathrm{~V}_{\text {BE (OFF) }}=-1.5 \mathrm{~V}, \\ & T_{A}=125^{\circ} \mathrm{C} \end{aligned}$ |  |  | 1.0 | mA |
| Emitter cutoff current | Iebo | $\mathrm{V}_{\text {EB }}=5.0 \mathrm{~V}, \mathrm{lc}=0 \mathrm{~A}$ |  |  | 10 | $\mu \mathrm{A}$ |
| DC current gain | $h_{\text {FE1 }}$ | $\mathrm{V}_{\text {CE }}=5.0 \mathrm{~V}, \mathrm{lc}=0.1 \mathrm{~A}^{\text {Note }}$ | 20 |  | 80 |  |
| DC current gain | hFE | $\mathrm{V}_{\text {CE }}=5.0 \mathrm{~V}, \mathrm{lc}=1.0 \mathrm{~A}^{\text {Note }}$ | 20 |  | 80 |  |
| DC current gain | hfe3 | $\mathrm{V}_{\text {CE }}=5.0 \mathrm{~V}, \mathrm{lc}=3.0 \mathrm{~A}^{\text {Note }}$ | 10 |  |  |  |
| Collector saturation voltage | $\mathrm{V}_{\text {CE(sat) }}$ | $\mathrm{Ic}=3.0 \mathrm{~A}, \mathrm{IB}=0.6 \mathrm{~A}^{\text {Note }}$ |  |  | 1.0 | V |
| Base saturation voltage | $\mathrm{V}_{\text {bE(sat) }}$ | $\mathrm{Ic}=3.0 \mathrm{~A}$, Is $=0.6 \mathrm{~A}^{\text {Note }}$ |  |  | 1.2 | V |
| Turn-on time | ton | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=3.0 \mathrm{~A}, \mathrm{R}_{\mathrm{L}}=50 \Omega, \\ & \mathrm{I}_{\mathrm{B} 1}=-\mathrm{I}_{\mathrm{B} 2}=0.6 \mathrm{~A}, \mathrm{~V} \mathrm{CC} \cong 150 \mathrm{~V} \\ & \text { Refer to the test circuit. } \end{aligned}$ |  |  | 1.0 | $\mu \mathrm{s}$ |
| Storage time | tstg |  |  |  | 2.5 | $\mu \mathrm{s}$ |
| Fall time | tf |  |  |  | 1.0 | $\mu \mathrm{S}$ |

Note Pulse test PW $\leq 350 \mu \mathrm{~s}$, duty cycle $\leq 2 \%$
hfe CLASSIFICATION

| Marking | M | L | K |
| :---: | :---: | :---: | :---: |
| hFE2 | 20 to 40 | 30 to 60 | 40 to 80 |

## SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



TYPICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ )




## PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)


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